

Four Output Differential Fanout Buffer for PCI Express Gen 1 & 2

ICS9DBL411A

Recommended Application:

PCI-Express fanout buffer

Output Features:

- 4 - low power differential output pairs
- Individual OE# control of each output pair

Key Specifications:

- Output cycle-cycle jitter < 25ps additive
- Output to output skew: < 50ps

Features/Benefits:

- Low power differential fanout buffer for PCI-Express and CPU clocks
- 20-pin MLF or TSSOP packaging

General Description:

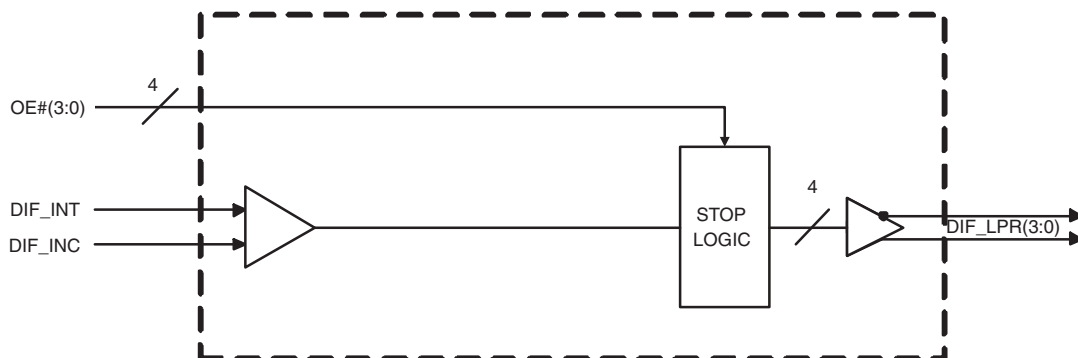
The **ICS9DBL411** is a 4 output lower power differential buffer. Each output has its own OE# pin. It has a maximum input frequency of 400 MHz.

Power Groups

Pin Number (TSSOP)		Description
VDD	GND	
9,18	10,17	VDD_IO for DIF(3:0)
4	5	3.3V Analog VDD & GND

Pin Number (MLF)		Description
VDD	GND	
6,15	7,14	VDD_IO for DIF(3:0)
1	2	3.3V Analog VDD & GND

Functional Block Diagram



TSSOP Pin Description

PIN # (TSSOP)	PIN NAME	PIN TYPE	DESCRIPTION
1	OE0#	IN	Output Enable for DIF0 output. Control is as follows: 0 = enabled, 1 = Low-Low
2	DIF_INC	IN	Complement side of differential input clock
3	DIF_INT	IN	True side of differential input clock
4	VDDA	PWR	3.3V Power for the Analog Core
5	GND A	GND	Ground for the Analog Core
6	OE3#	IN	Output Enable for DIF3 output. Control is as follows: 0 = enabled, 1 = Low-Low
7	DIF3C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
8	DIF3T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
9	VDD_IO	PWR	Power supply for low power differential outputs, nominal 1.05V to 3.3V
10	GND	GND	Ground pin
11	DIF2C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
12	DIF2T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
13	OE2#	IN	Output Enable for DIF2 output. Control is as follows: 0 = enabled, 1 = Low-Low
14	DIF1C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
15	DIF1T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
16	OE1#	IN	Output Enable for DIF1 output. Control is as follows: 0 = enabled, 1 = Low-Low
17	GND	GND	Ground pin
18	VDD_IO	PWR	Power supply for low power differential outputs, nominal 1.05V to 3.3V
19	DIF0C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
20	DIF0T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)

MLF Pin Description

PIN # (MLF)	PIN NAME	PIN TYPE	DESCRIPTION
1	VDDA	PWR	3.3V Power for the Analog Core
2	GNDA	GND	Ground for the Analog Core
3	OE3#	IN	Output Enable for DIF3 output. Control is as follows: 0 = enabled, 1 = Low-Low
4	DIF3C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
5	DIF3T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
6	VDD_IO	PWR	Power supply for low power differential outputs, nominal 1.05V to 3.3V
7	GND	GND	Ground pin
8	DIF2C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
9	DIF2T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
10	OE2#	IN	Output Enable for DIF2 output. Control is as follows: 0 = enabled, 1 = Low-Low
11	DIF1C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
12	DIF1T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
13	OE1#	IN	Output Enable for DIF1 output. Control is as follows: 0 = enabled, 1 = Low-Low
14	GND	GND	Ground pin
15	VDD_IO	PWR	Power supply for low power differential outputs, nominal 1.05V to 3.3V
16	DIF0C_LPR	OUT	Complement clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
17	DIF0T_LPR	OUT	True clock of low power differential clock pair. (no 50ohm shunt resistor to GND needed)
18	OE0#	IN	Output Enable for DIF0 output. Control is as follows: 0 = enabled, 1 = Low-Low
19	DIF_INC	IN	Complement side of differential input clock
20	DIF_INT	IN	True side of differential input clock

Absolute Maximum Ratings

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS	Notes
Maximum Supply Voltage	VDDA	Core Supply Voltage		4.6	V	1,7
Maximum Supply Voltage	VDD_IO	Low-Voltage Differential I/O Supply	0.99	3.8	V	1,7
Maximum Input Voltage	V _{IH}	3.3V LVCMOS Inputs		4.6	V	1,7,8
Minimum Input Voltage	V _{IL}	Any Input	V _{SS} - 0.5		V	1,7
Storage Temperature	T _s	-	-65	150	°C	1,7
Input ESD protection	ESD prot	Human Body Model	2000		V	1,7

Electrical Characteristics - Input/Supply/Common Output Parameters

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS	Notes
Ambient Operating Temp	T _{ambient}	-	0	70	°C	1
Supply Voltage	VDDxxx	Supply Voltage	3.135	3.465	V	1
Supply Voltage	VDDxxx_IO	Low-Voltage Differential I/O Supply	0.99	3.465	V	1
Input High Voltage	V _{IHSE}	Single-ended inputs	2	V _{DD} + 0.3	V	1
Input Low Voltage	V _{ILSE}	Single-ended inputs	V _{SS} - 0.3	0.8	V	1
Differential Input High Voltage	V _{IHDIF}	Differential inputs (single-ended measurement)	600	1.15	V	1
Differential Input Low Voltage	V _{ILDIF}	Differential inputs (single-ended measurement)	V _{SS} - 0.3	300	mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4	8	V/ns	2
Input Leakage Current	I _{IN}	V _{IN} = V _{DD} , V _{IN} = GND	-5	5	uA	1
Operating Supply Current	I _{DD_3.3V}	3.3V supply		25	mA	1
	I _{DD_IO+100M}	VDD_IO supply @ fOP = 100MHz		15	mA	1
	I _{DD_IO_400M}	VDD_IO supply @ fOP = 400MHz		54	mA	1
Standby Current	I _{DD_SB33}	3.3V supply, Input stopped, OE# pins all high		1	mA	1
	I _{DD_SBio}	VDD_IO supply, Input stopped		0.1	mA	1
Input Frequency	F _i	V _{DD} = 3.3 V	33	400	MHz	2
Pin Inductance	L _{pin}			7	nH	1
Input Capacitance	C _{IN}	Logic Inputs	1.5	5	pF	1
	C _{OUT}	Output pin capacitance		6	pF	1
OE# latency	T _{OE#LAT}	Number of clocks to enable or disable output from assertion/deassertion of OE#	1	3	periods	1
Tdrive_OE#	T _{DROE#}	Output enable after OE# de-assertion		10	ns	1
Tfall_OE#	T _{FALL}	Fall/rise time of OE# inputs		5	ns	1
Trise_OE#	T _{RISE}			5	ns	1

AC Electrical Characteristics - DIF Low Power Differential Outputs

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS	NOTES
Rising Edge Slew Rate	t_{SLR}	Differential Measurement	1	2.5	V/ns	1,2
Falling Edge Slew Rate	t_{FLR}	Differential Measurement	1	2.5	V/ns	1,2
Slew Rate Variation	t_{SLVAR}	Single-ended Measurement		20	%	1
Maximum Output Voltage	V_{HIGH}	Includes overshoot		1150	mV	1
Minimum Output Voltage	V_{LOW}	Includes undershoot	-300		mV	1
Differential Voltage Swing	V_{SWING}	Differential Measurement	1200		mV	1
Crossing Point Voltage	V_{XABS}	Single-ended Measurement	300	550	mV	1,3,4
Crossing Point Variation	$V_{XABSVAR}$	Single-ended Measurement		140	mV	1,3,5
Duty Cycle Distortion	$D_{CYCDIS0}$	Differential Measurement, $f_{IN} \leq 100\text{MHz}$		0.5	%	1,6
	$D_{CYCDIS1}$	Differential Measurement $100\text{MHz} < f_{IN} \leq 267\text{MHz}$		+5	%	1,6
	$D_{CYCDIS2}$	Differential Measurement, $f_{IN} > 267\text{MHz}$		+7	%	1,6
DIF Jitter - Cycle to Cycle	$DIFJ_{C2C}$	Differential Measurement, Additive		25	ps	1
DIF[3:0] Skew	DIF_{SKEW}	Differential Measurement		50	ps	1
Propagation Delay	t_{PD}	Input to output Delay	2.5	3.5	ns	1
PCIe Gen2 Phase Jitter - Additive	t_{phase_addHI}	$1.5\text{MHz} < f_{IN} < \text{Nyquist} (50\text{MHz})$		0.8	ps rms	1
PCIe Gen2 Phase Jitter - Additive	t_{phase_addLO}	$10\text{KHz} < f_{IN} < 1.5\text{MHz}$		0.1	ps rms	1

Notes on Electrical Characteristics:

¹Guaranteed by design and characterization, not 100% tested in production.

²Slew rate measured through Vswing centered around differential zero

³Vxabs is defined as the voltage where CLK = CLK#

⁴Only applies to the differential rising edge (CLK rising and CLK# falling)

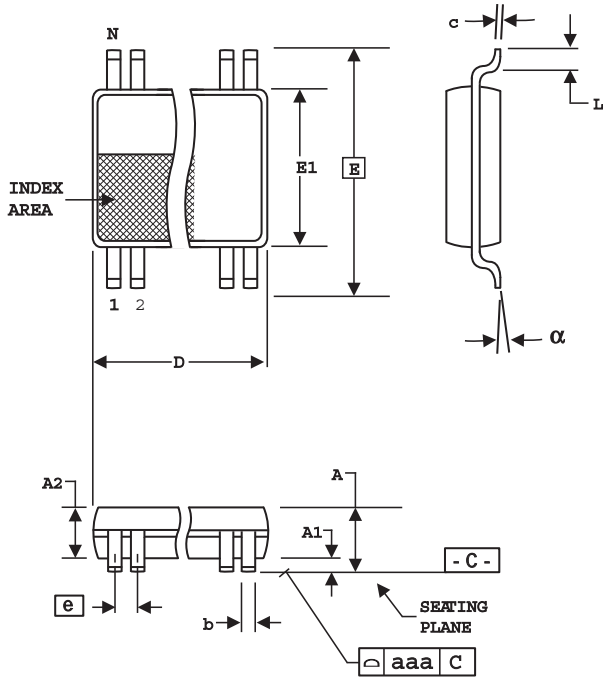
⁵Defined as the total variation of all crossing voltages of CLK rising and CLK# falling. Matching applies to rising edge rate of CLK and falling edge of CLK#. It is measured using a +/-75mV window centered on the average cross point where CLK meets CLK#.

⁶This is the figure refers to the maximum distortion of the input wave form.

⁷Operation under these conditions is neither implied, nor guaranteed.

⁸Maximum input voltage is not to exceed maximum VDD

20-pin TSSOP Package Drawing and Dimensions



20-Lead, 4.40 mm. Body, 0.65 mm. Pitch TSSOP
(173 mil) (25.6 mil)

SYMBOL	In Millimeters		In Inches	
	COMMON DIMENSIONS	COMMON DIMENSIONS	COMMON DIMENSIONS	COMMON DIMENSIONS
A	--	1.20	--	.047
A1	0.05	0.15	.002	.006
A2	0.80	1.05	.032	.041
b	0.19	0.30	.007	.012
c	0.09	0.20	.0035	.008
D	SEE VARIATIONS		SEE VARIATIONS	
E	6.40 BASIC		0.252 BASIC	
E1	4.30	4.50	.169	.177
e	0.65 BASIC		0.0256 BASIC	
L	0.45	0.75	.018	.030
N	SEE VARIATIONS		SEE VARIATIONS	
a	0°	8°	0°	8°
aaa	--	0.10	--	.004

VARIATIONS

N	D mm.		D (inch)	
	MIN	MAX	MIN	MAX
20	6.40	6.60	.252	.260

Reference Doc.: JEDEC Publication 95, MO-153

10-0035

Revision History

Rev.	Issue Date	Description	Page #
0.1	8/1/2006	Initial Release.	-
0.2	9/22/2006	Updated MLF Package Dimensions.	8
A	7/31/2007	1. Updated electrical characteristics - additive jitter, cycle-to-cycle, tpd, skews, slew rates, Idd, etc. 2. Corrected power grouping table for TSSOP pkg 3. Final Release	1,5,6
B	2/21/2008	1. Highlighted that V_{IHDIF} and V_{ILDIF} are single ended measurments. 2. Corrected VSWING paramater from 300mV to 1200mV. 3. Updated duty cycle distortion table with a 3rd figure for speeds $\leq 100\text{MHz}$.	5
C	6/28/2012	Typo for "Differential Input Low Voltage" units; changed "V" to "mV"	

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